

Porous and single crystalline Co_3O_4 nanospheres for pseudocapacitors with enhanced performances

Yuyin Gong,^a Feilong Gong,^a Chaofei Wang,^a Hegen Zheng^b and Feng Li^{*a,c}

^a State Laboratory of Surface and Interface Science and Technology, Collaborative Innovation Center of Environmental Pollution Control and Ecological Restoration, Zhengzhou University of Light Industry, Zhengzhou 450001, China

Fax: 86-371-86609676; Tel: 86-371-86609676; E-mail: fengli@zzuli.edu.cn; lifeng696@yahoo.com

^b State Key Laboratory of Coordination Chemistry, Nanjing University
Nanjing 210093, Jiangsu, China

^c American Advanced Nanotechnology, Houston, TX 77459, USA
E-mail: lifeng696@yahoo.com

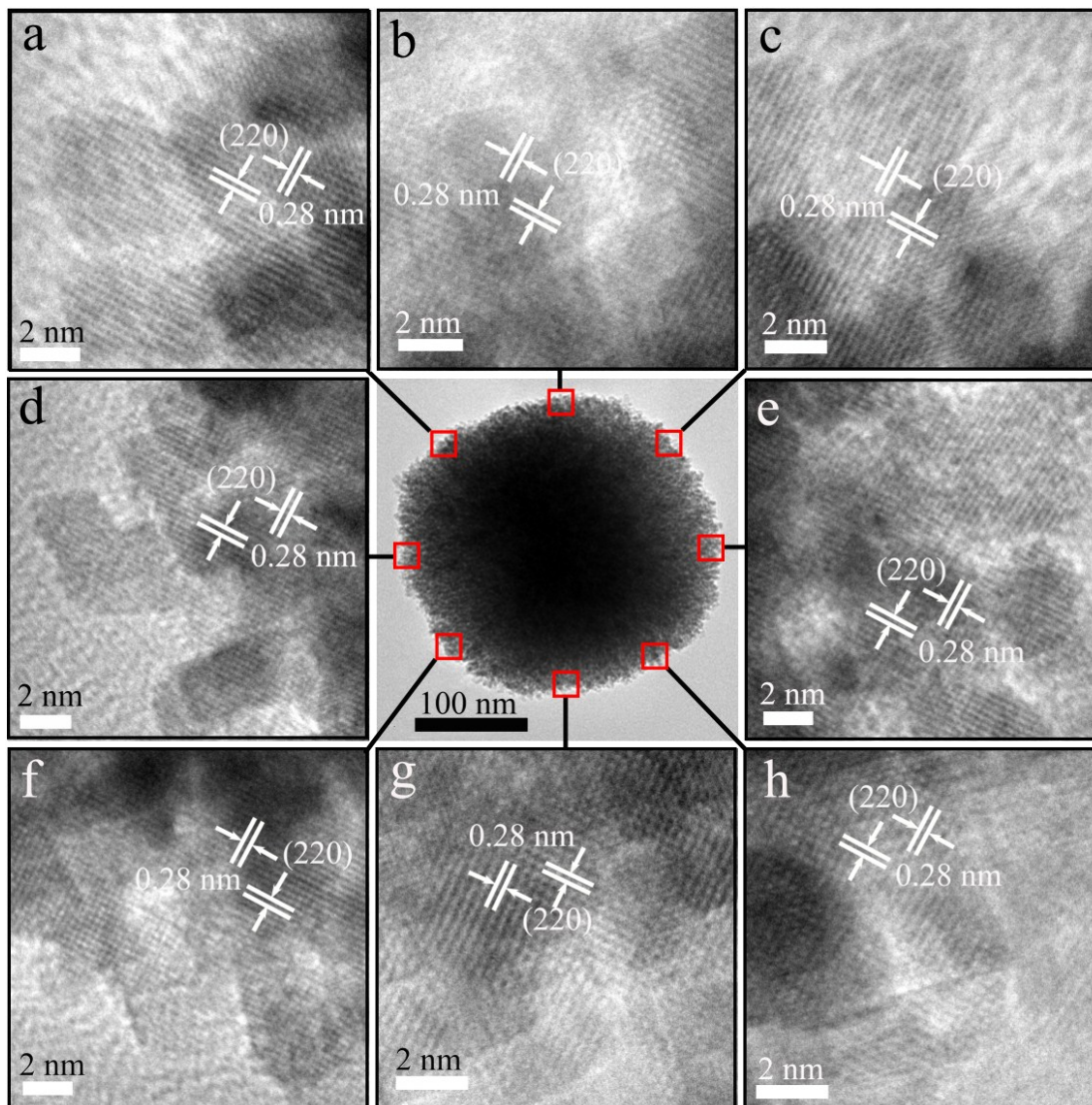


Fig. S1. HRTEM images (a-h) taken around the edge of a Co₃O₄ hemisphere.

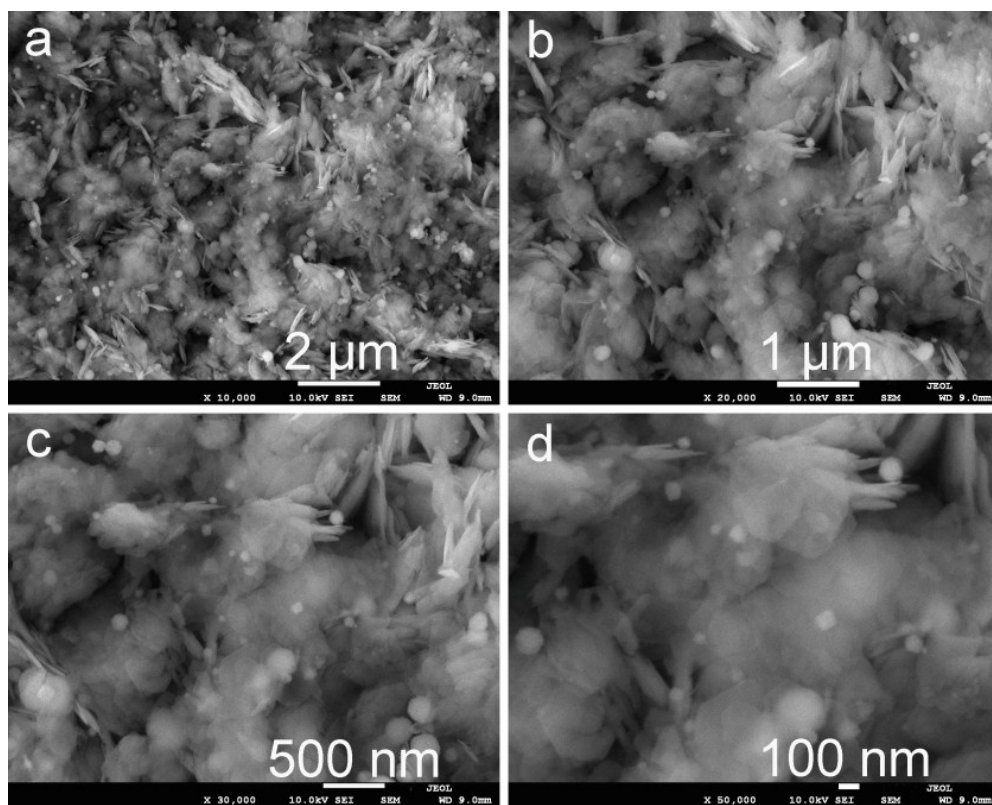


Fig. S2. FESEM images of materials after reacting for 3 hours.

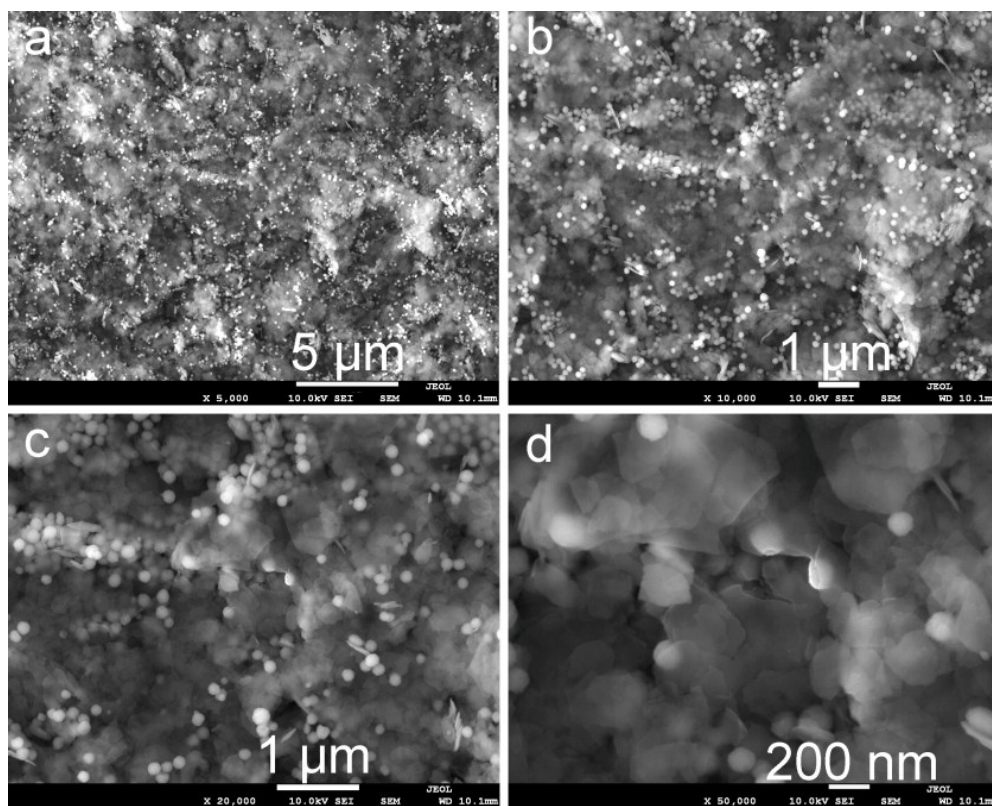


Fig. S3. FESEM images of materials after reacting for 4 hours.

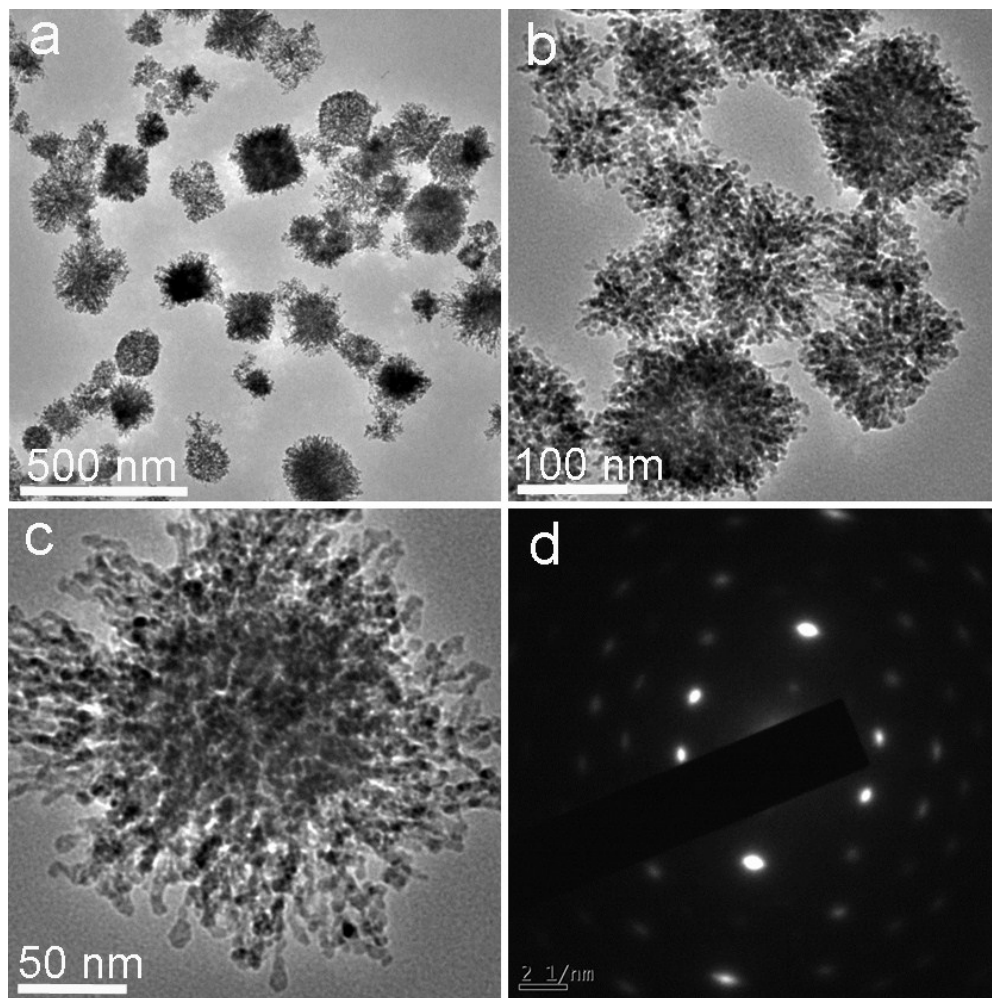


Fig. S4. (a-c) TEM images of 3D dendritic Co_3O_4 nanoparticles after reacting for 6 hours and (d) SAED pattern of a particles as shown in (c).

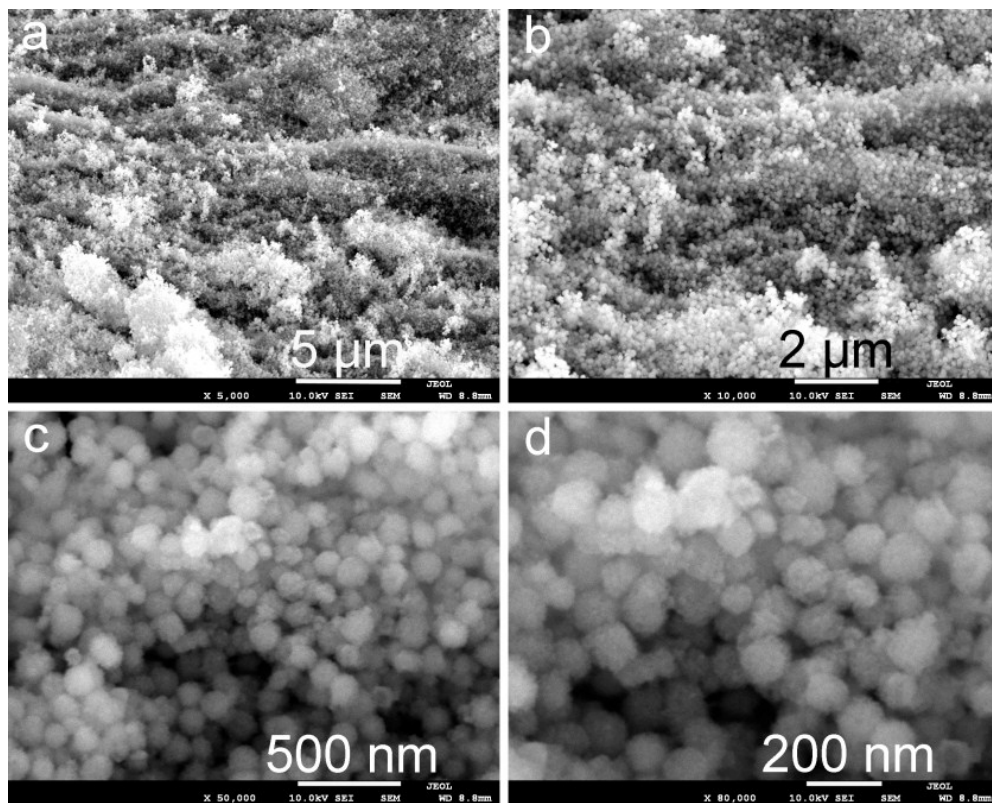


Fig. S5. FESEM images of 3D dendritic Co_3O_4 nanoparticles after reacting for 6 hours

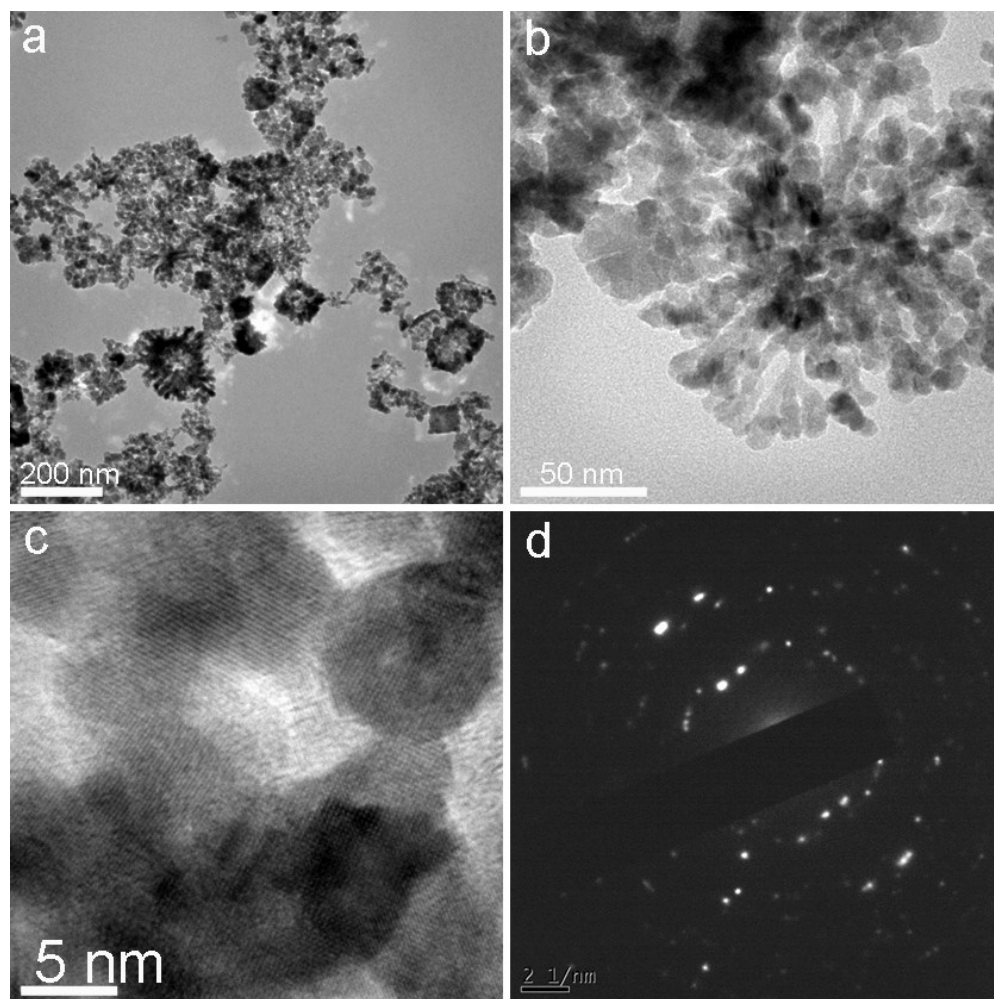


Fig. S6. (a,b) TEM and (c) HRTEM images of Co_3O_4 nanoparticles after reacting for 11 hours. (d) The SAED pattern of the particles as shown in (b).

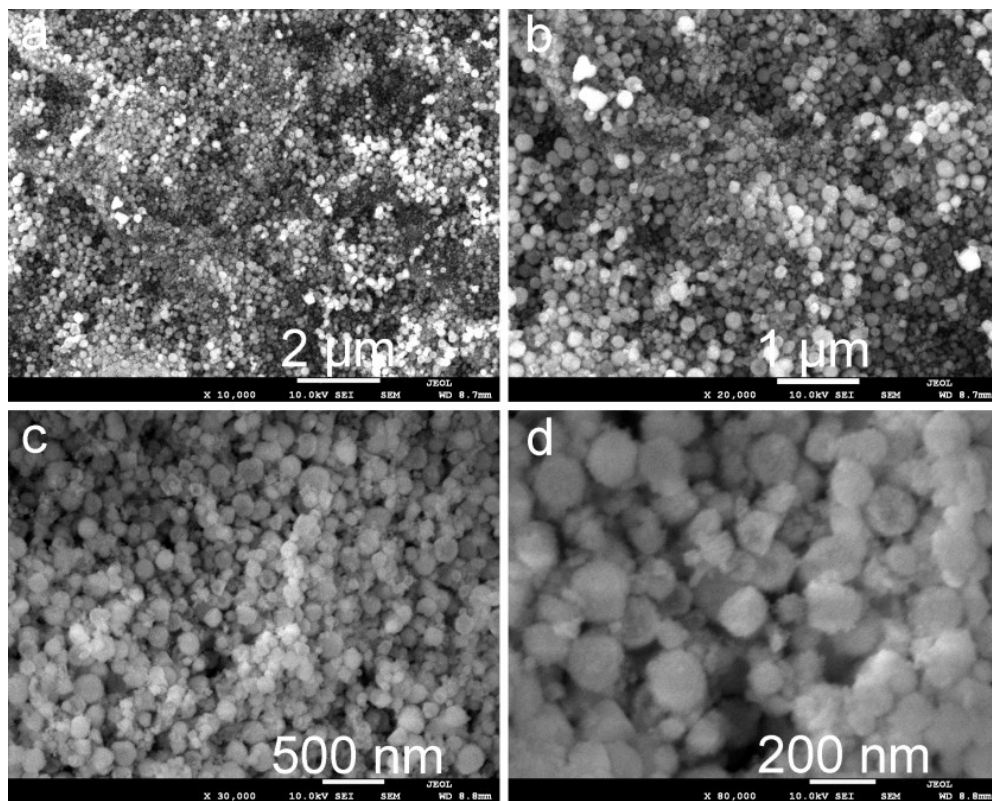


Fig. S7. SEM images of Co_3O_4 nanoparticles after reacting for 11 hours.

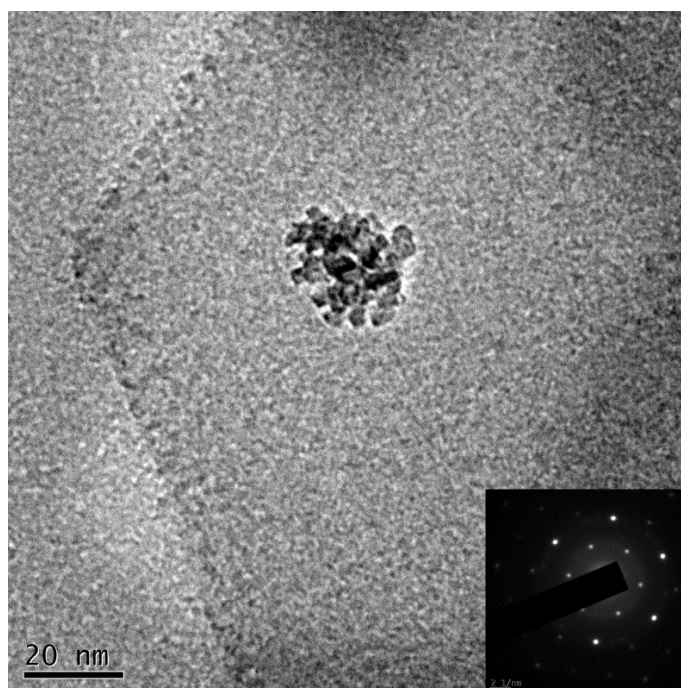


Fig. S8. TEM image of a nanojenga on the surface of nanosheets. The inset: SAED pattern of the area.

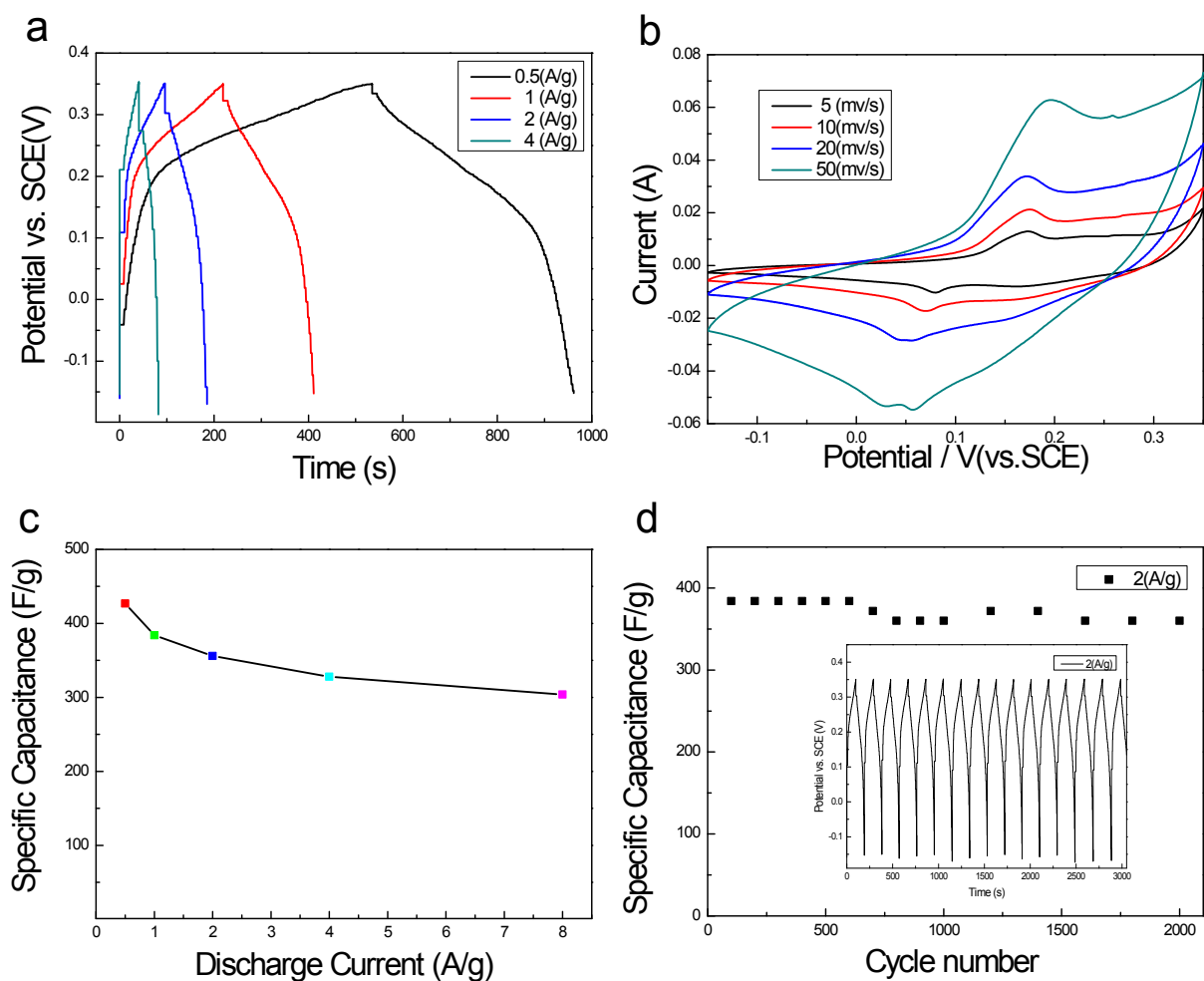


Fig. S9. Charge storage performances of Co_3O_4 nanoparticles produced by reacting for 6 hours. a) CV curves of the electrode in 6.0 M KOH at different scan rates. b) The charge-discharge curves of the capacitors measured at different current densities. c) Average specific capacitance of the devices at various discharge current densities. d) Average specific capacitance versus cycle number of supercapacitors at a galvanostatic charge-discharge current density of 4 A g^{-1} , the insets show the galvanostatic charge-discharge curves of the device at a current density of 4 A g^{-1} .